

PolarHV™ HiPerFET Power MOSFET

N-Channel Enhancement Mode
Fast Recovery Diode
Avalanche Rated

IXFH 30N60P
IXFT 30N60P
IXFV 30N60P
IXFV 30N60PS

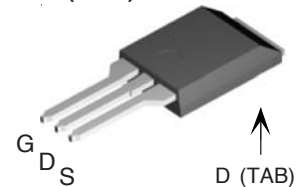
$V_{DSS} = 600$ V
 $I_{D25} = 30$ A
 $R_{DS(on)} \leq 240$ mΩ
 $t_{rr} \leq 250$ ns



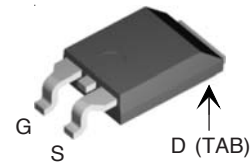
Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ MΩ	600	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	$T_C = 25^\circ\text{C}$	30	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	80	A
I_{AR}	$T_C = 25^\circ\text{C}$	30	A
E_{AR}	$T_C = 25^\circ\text{C}$	50	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/μs, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4$ Ω	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	500	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s Plastic body	300 260	°C °C
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	5	g
	PLUS220	4	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 250$ μA	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 30$ V, $V_{DS} = 0$			±100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0$ V $T_J = 125^\circ\text{C}$			25 μA
				250 μA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300$ μs, duty cycle $d \leq 2\%$			240 mΩ

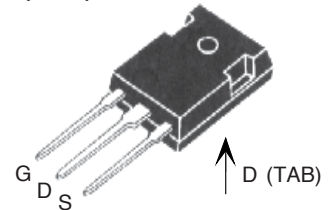
PLUS220 (IXFV)



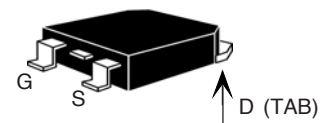
PLUS220 (IXFV...S)



TO-247 (IXFH)



TO-268 (IXFT)



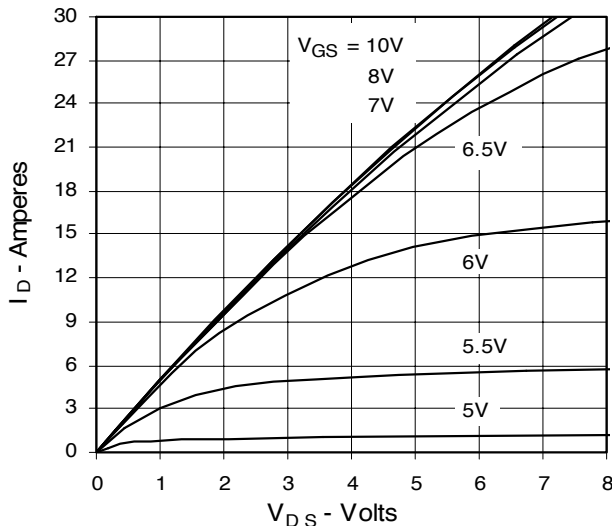
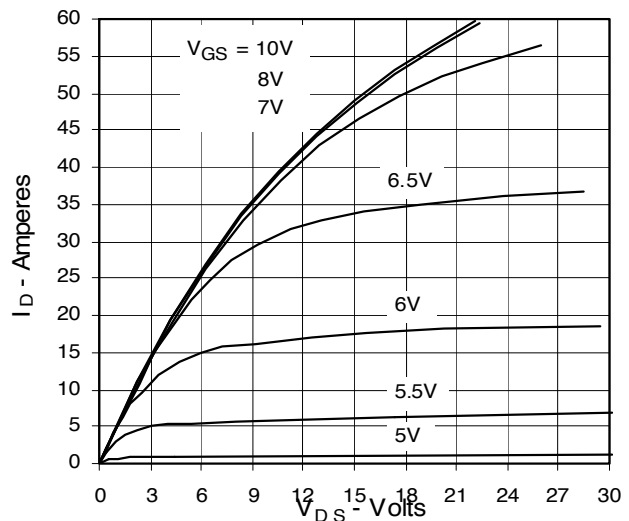
G = Gate D = Drain
S = Source TAB = Drain

Features

- Fast Recovery diode
- Unclamped Inductive Switching (UIS) rated
- International standard packages
- Low package inductance
- easy to drive and to protect

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 20 V; I _D = 0.5 I _{D25} , pulse test	15	27	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		4000	pF
C_{oss}			430	pF
C_{rss}			42	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 I _{D25} R _G = 4 Ω (External)		29	ns
t_r			20	ns
t_{d(off)}			80	ns
t_f			25	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}		145	nC
Q_{gs}			30	nC
Q_{gd}			75	nC
R_{thJC}	TO-247, PLUS220			0.25 KW
R_{thCK}			0.21	KW

Source-Drain Diode		Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	V _{GS} = 0 V			30 A
I_{SM}	Repetitive			80 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t_{rr}	I _F = 25A, -di/dt = 100 A/μs V _R = 100V			250 ns
Q_{RM}			0.8	

Fig. 1. Output Characteristics @ 25°C

Fig. 2. Extended Output Characteristics @ 25°C


IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	

Fig. 3. Output Characteristics @ 125°C

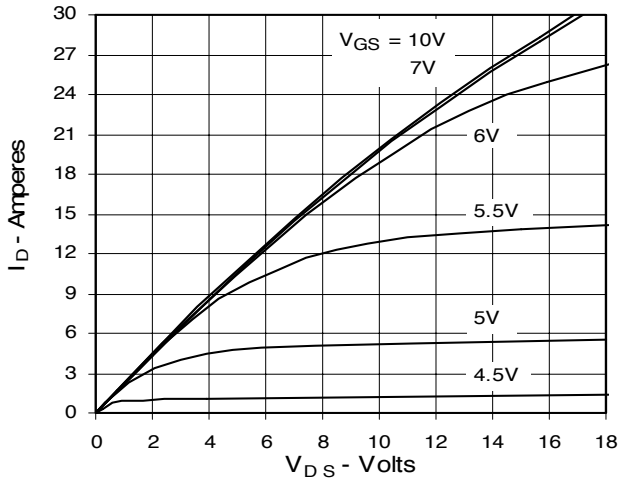


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

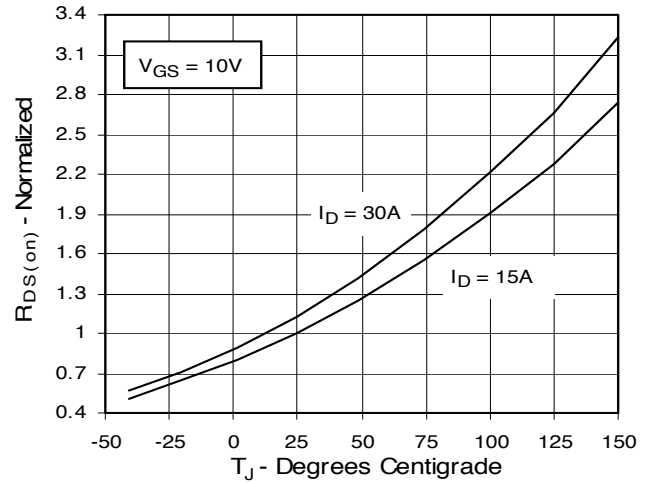


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

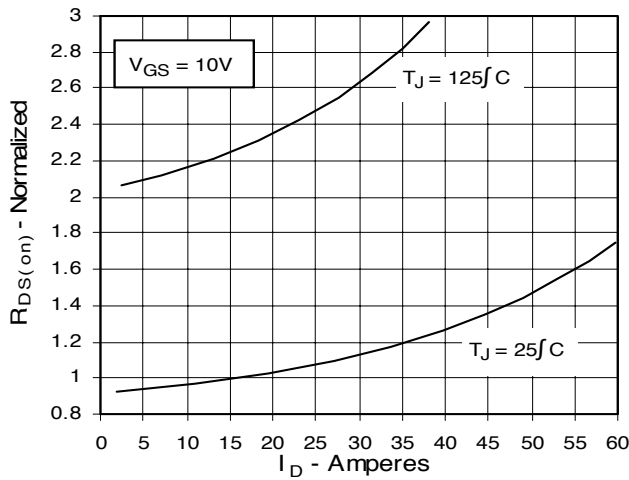


Fig. 6. Drain Current vs. Case Temperature

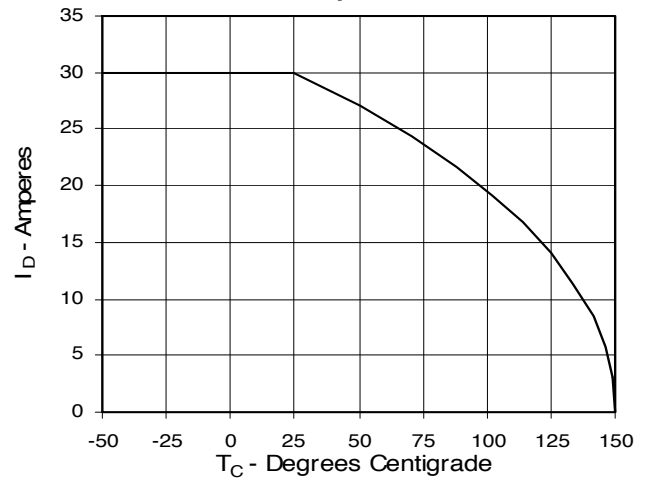


Fig. 7. Input Admittance

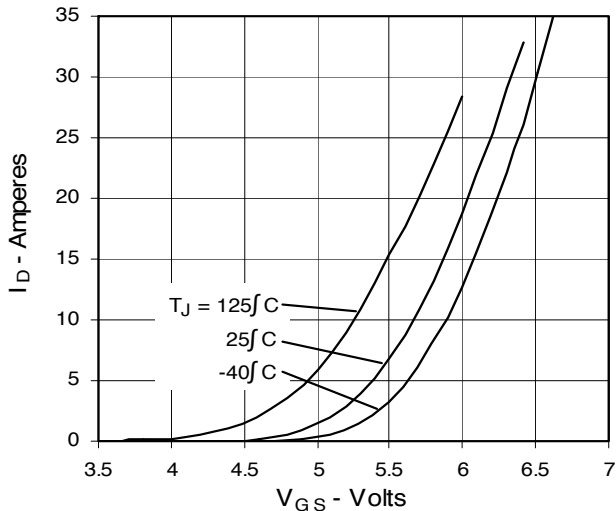


Fig. 8. Transconductance

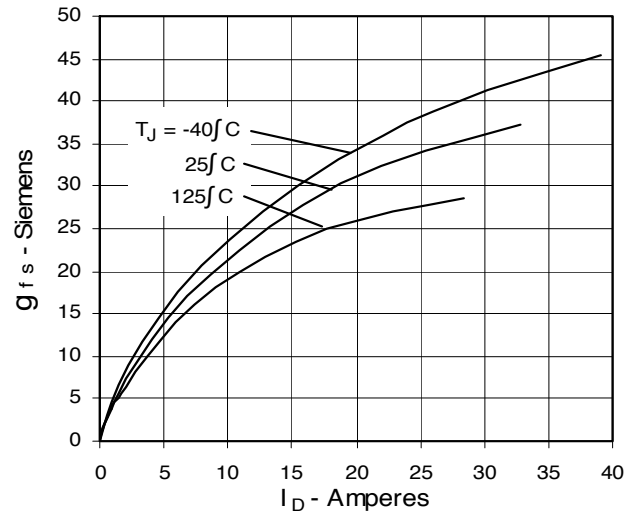


Fig. 9. Source Current vs. Source-To-Drain Voltage

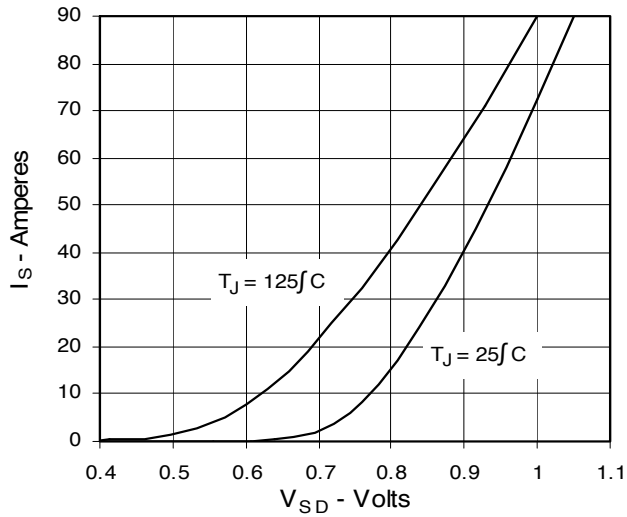


Fig. 10. Gate Charge

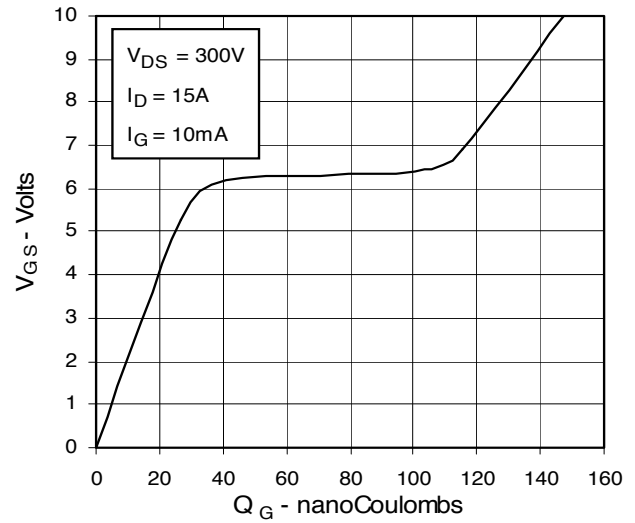


Fig. 11. Capacitance

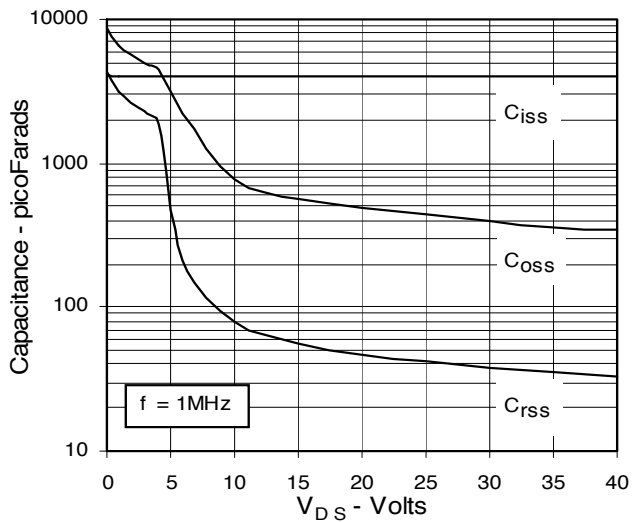
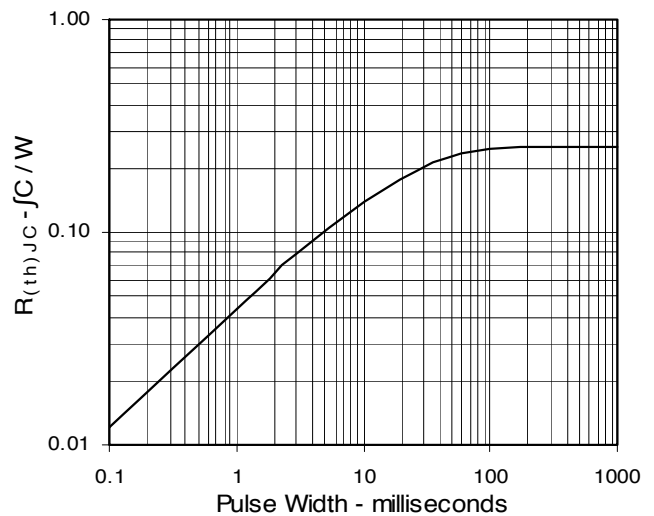
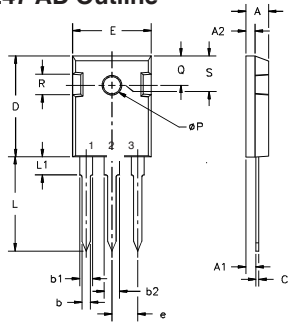


Fig. 12. Maximum Transient Thermal Resistance



Package Outline Drawings

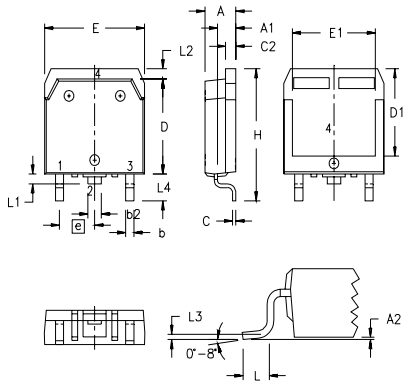
TO-247 AD Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

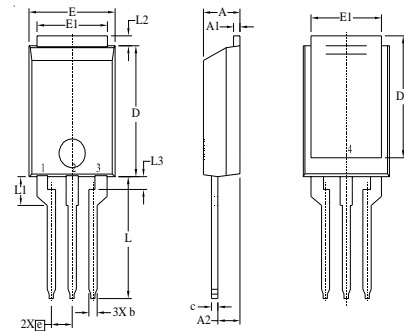
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 (IXTT) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010 BSC		0.25 BSC	
L ₄	.150	.161	3.80	4.10

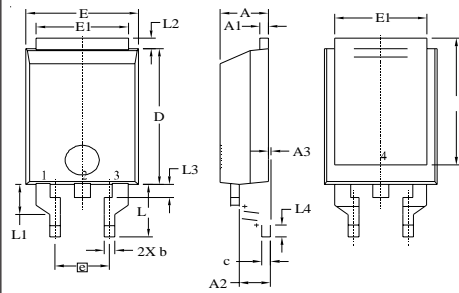
PLUS220 (IXFV) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source TAB - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A ₁	.028	.035	0.70	0.90
A ₂	.098	.118	2.50	3.00
b	.035	.047	0.90	1.20
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D ₁	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E ₁	.331	.346	8.40	8.80
e	.100 BSC		2.54 BSC	
L	.512	.551	13.00	14.00
L ₁	.118	.138	3.00	3.50
L ₂	.035	.051	0.90	1.30
L ₃	.047	.059	1.20	1.50

PLUS220 (IXFV..S) Outline



Terminals: 1-Gate 2-Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A ₁	.028	.035	0.70	0.90
A ₂	.098	.118	2.50	3.00
A ₃	.000	.010	0.00	0.25
b	.035	.047	0.90	1.20
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D ₁	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E ₁	.331	.346	8.40	8.80
e	.200BSC		5.08 BSC	
L	.209	.228	5.30	5.80
L ₁	.118	.138	3.00	3.50
L ₂	.035	.051	0.90	1.30
L ₃	.047	.059	1.20	1.50
L ₄	.039	.059	1.00	1.50